

Fig. 1A

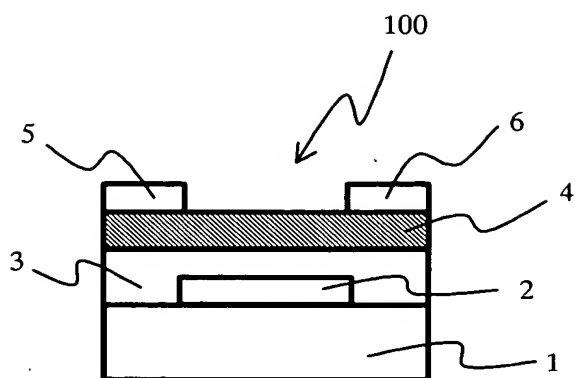


Fig. 1B

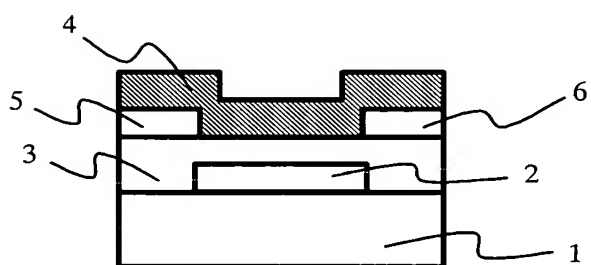


Fig. 1C

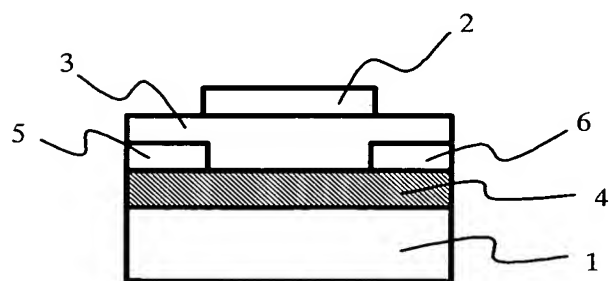


Fig. 1D

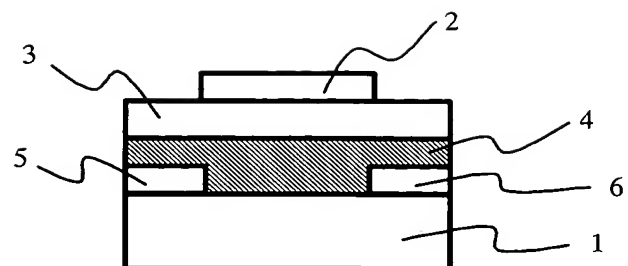


Fig. 2A

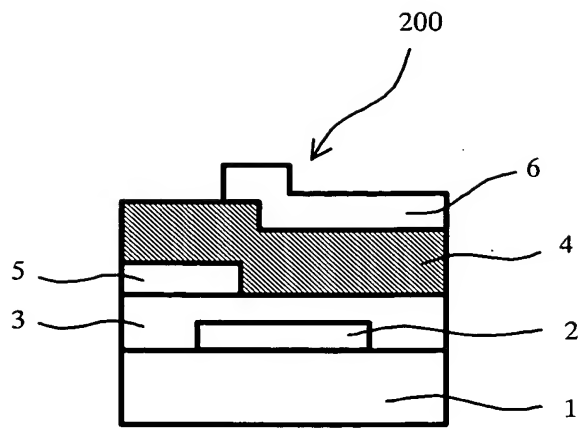
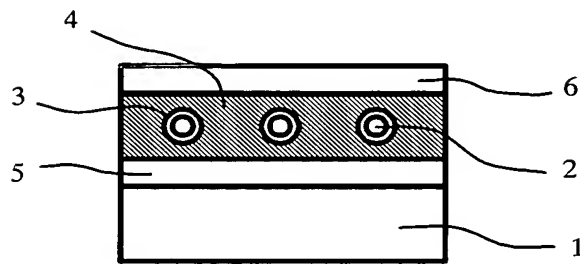


Fig. 2B



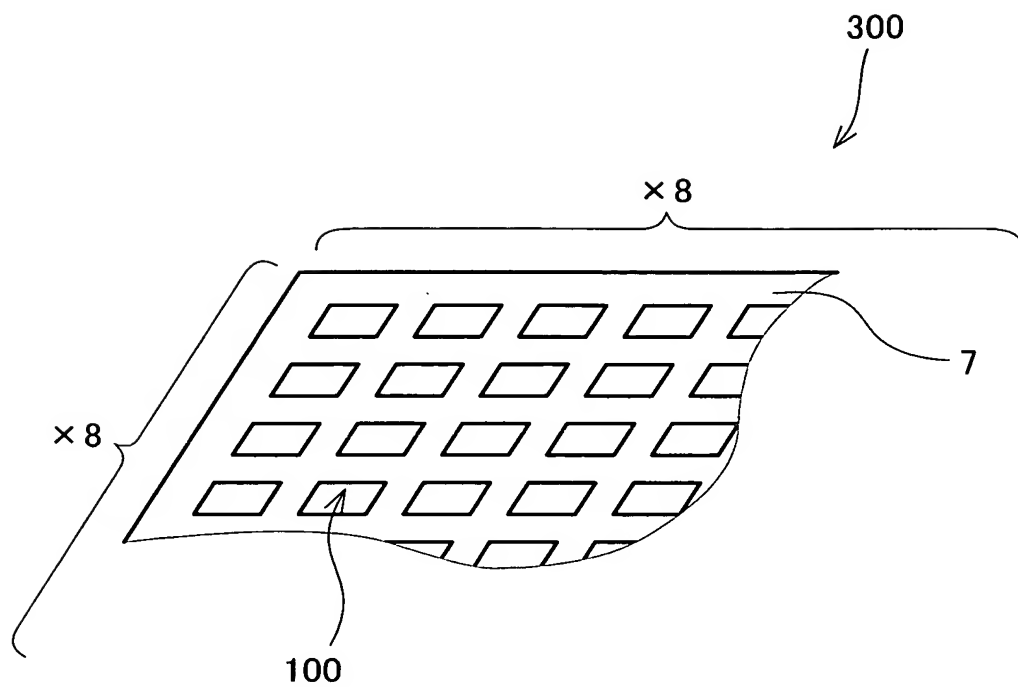


Fig. 3

Fig. 4A

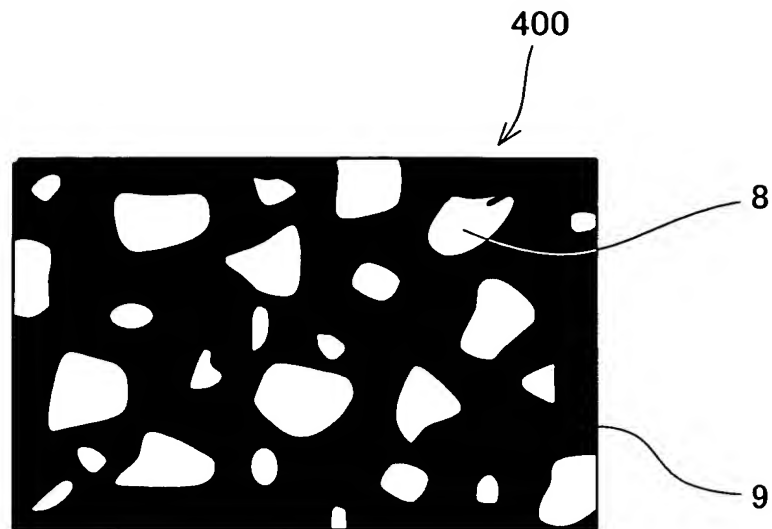
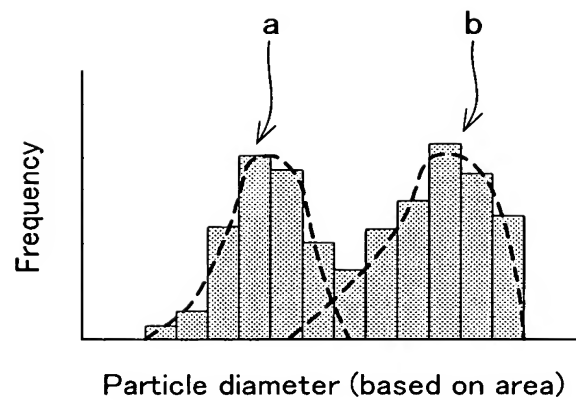


Fig. 4B



P-type silicon crystal 1 Average particle diameter 20 μ m (volume%)	P-type silicon crystal 2 Average particle diameter 1.5 μ m (volume%)	Total filling rate (volume%)
0	0	0
10	0	10
20	0	20
40	0	40
40	15	55
40	20	60
40	25	65

Fig. 5

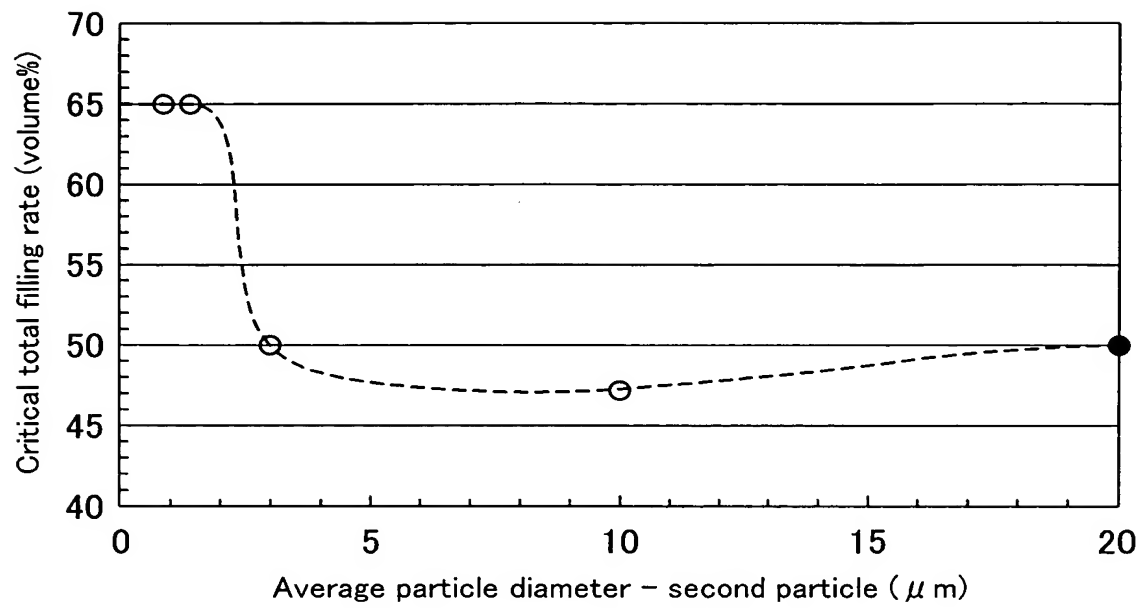


Fig. 6

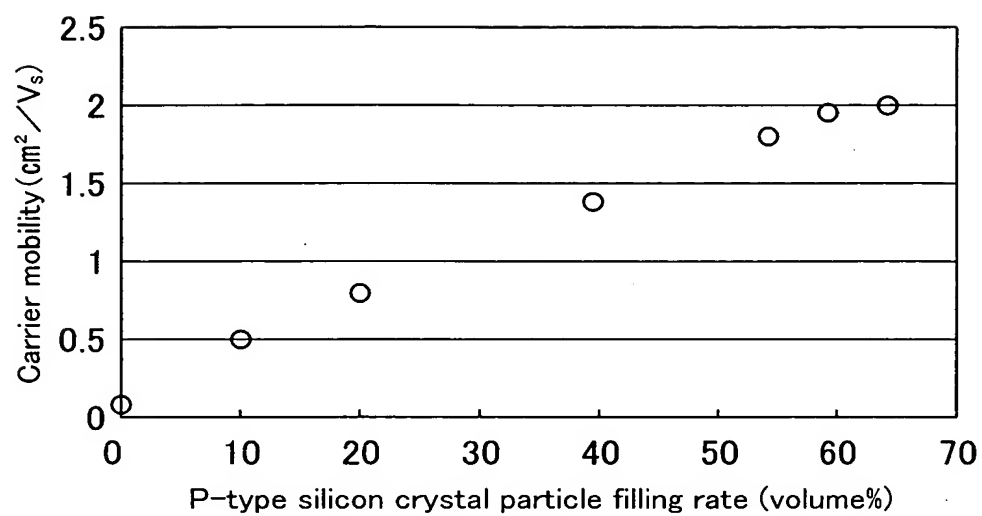


Fig. 7

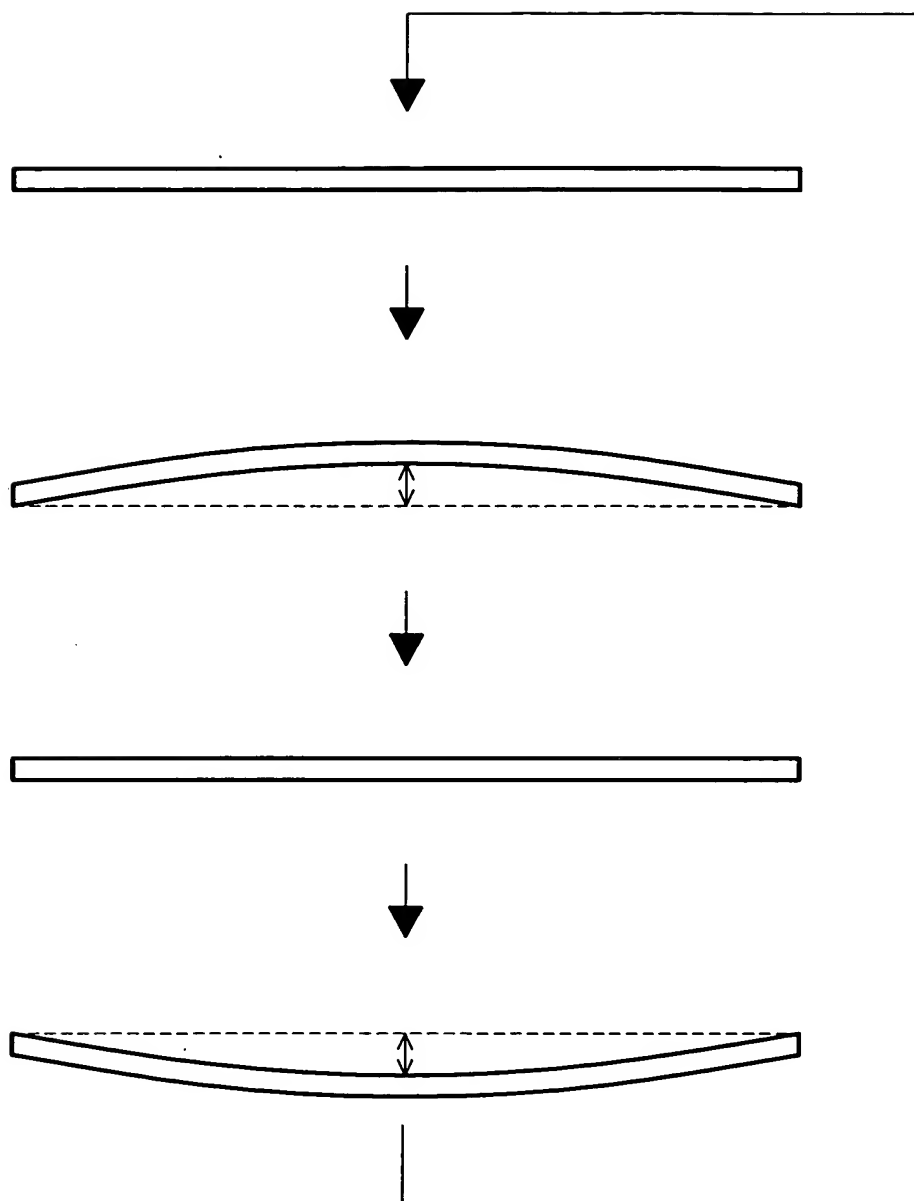


Fig. 8

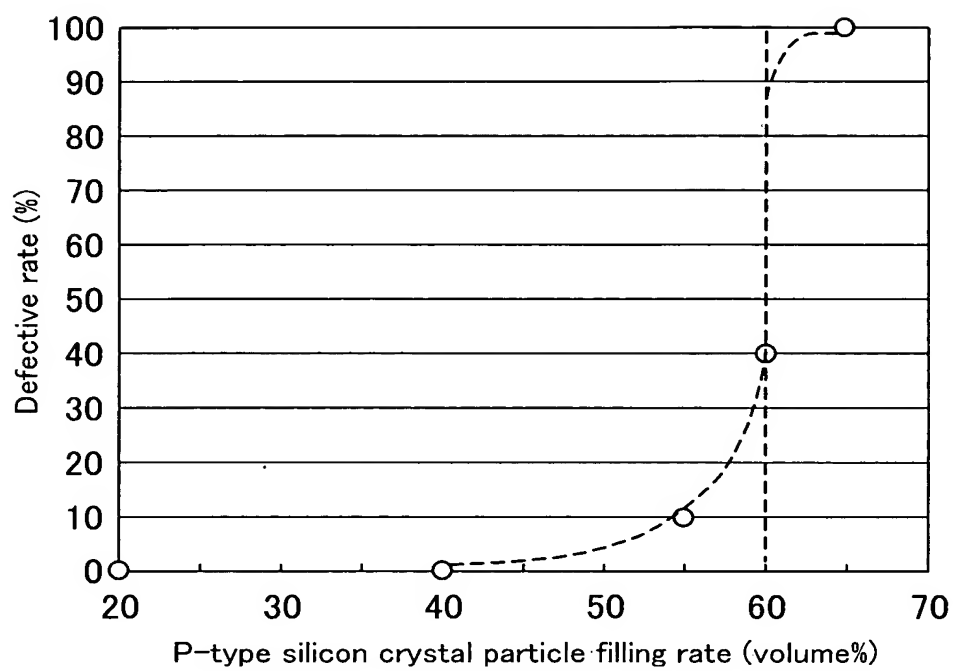


Fig. 9

Cu particle 1 Average particle diameter 10 μ m (volume%)	Cu particle 2 Average particle diameter 1 μ m (volume%)	Total filling rate (volume%)
0	0	0
10	0	10
30	0	30
40	5	45
40	20	60

Fig. 10

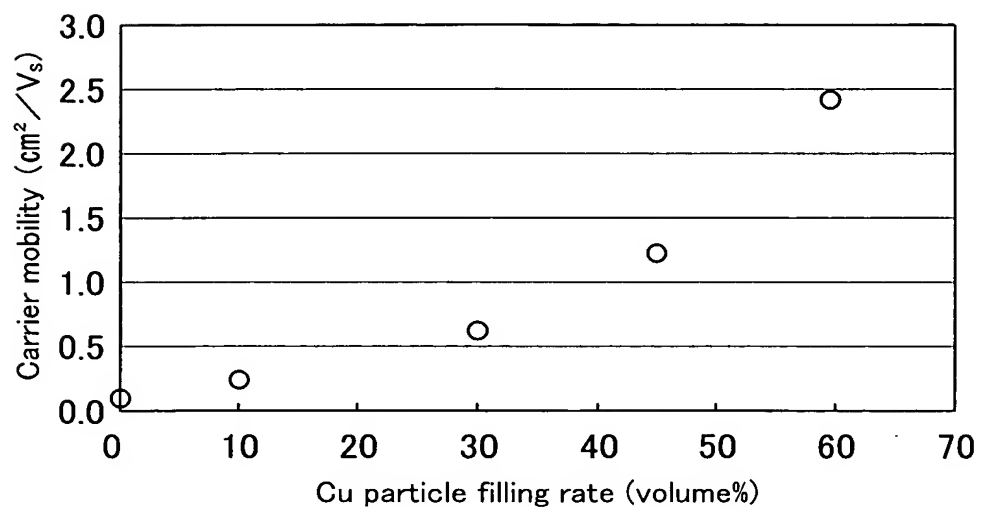


Fig. 11

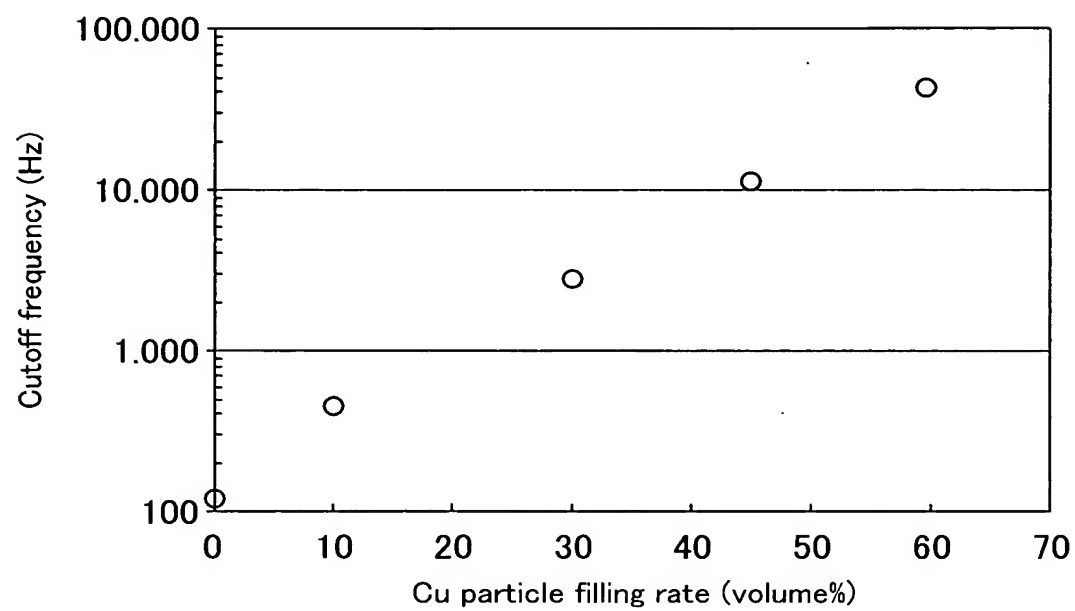


Fig. 12

	P-type silicon crystal 1 Average particle diameter 20 μ m (volume%)	Cu particle 2 Average particle diameter 1 μ m (volume%)	Total filling rate (volume%)	Carrier mobility (cm^2/Vs)	Cutoff frequency (kHz)
1st embodiment	40	0	40	1.4	2.2
3rd embodiment(1)	40	5	45	1.9	4.7
3rd embodiment(2)	40	10	50	2.5	8.5

Fig. 13

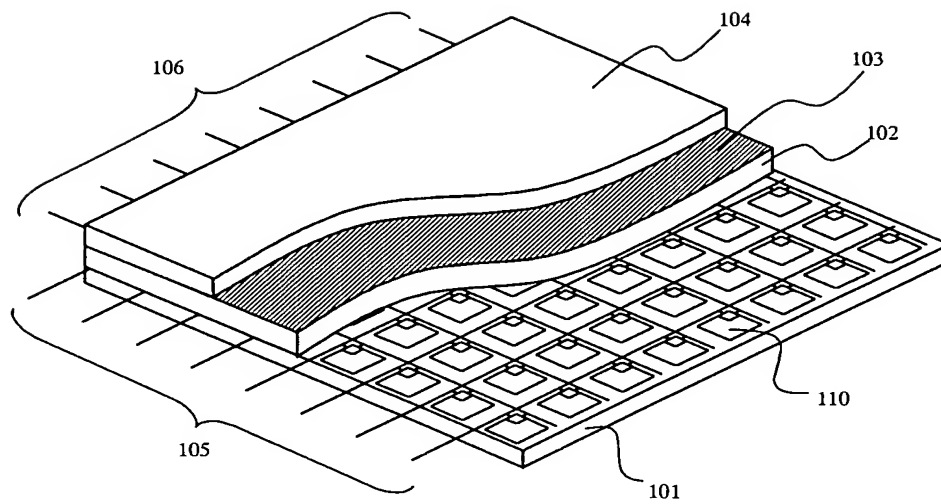


Fig. 14

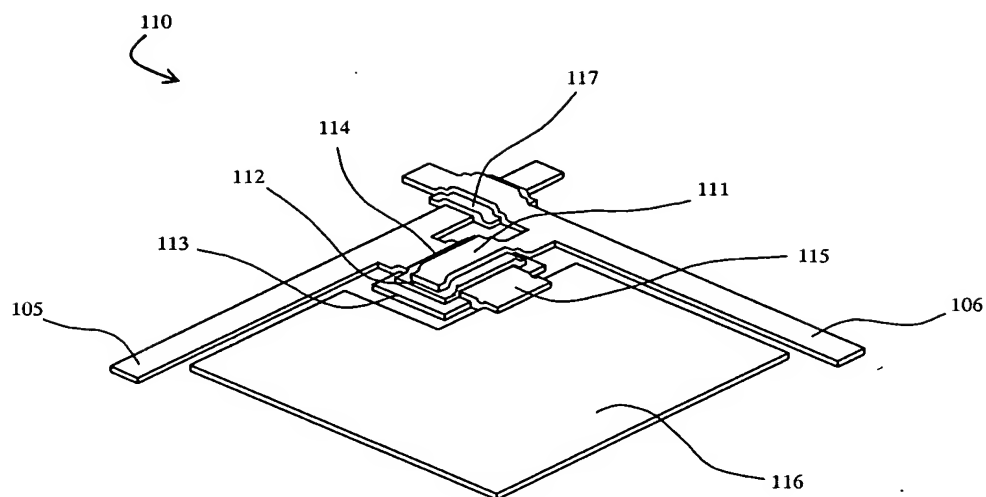


Fig. 15

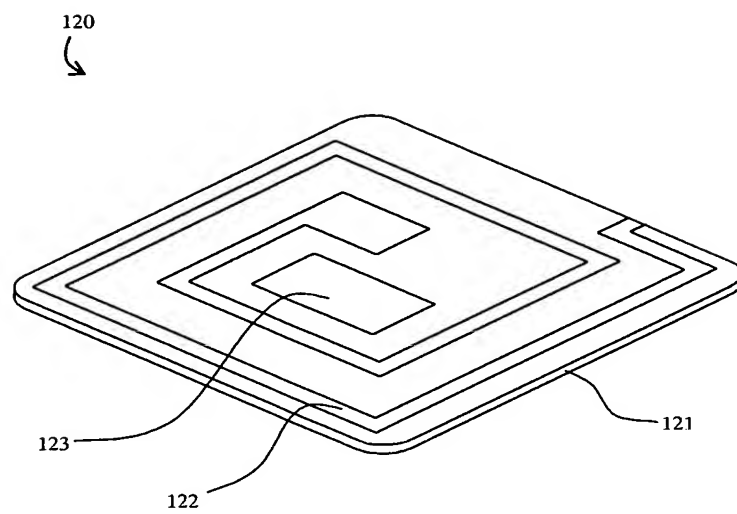


Fig. 16

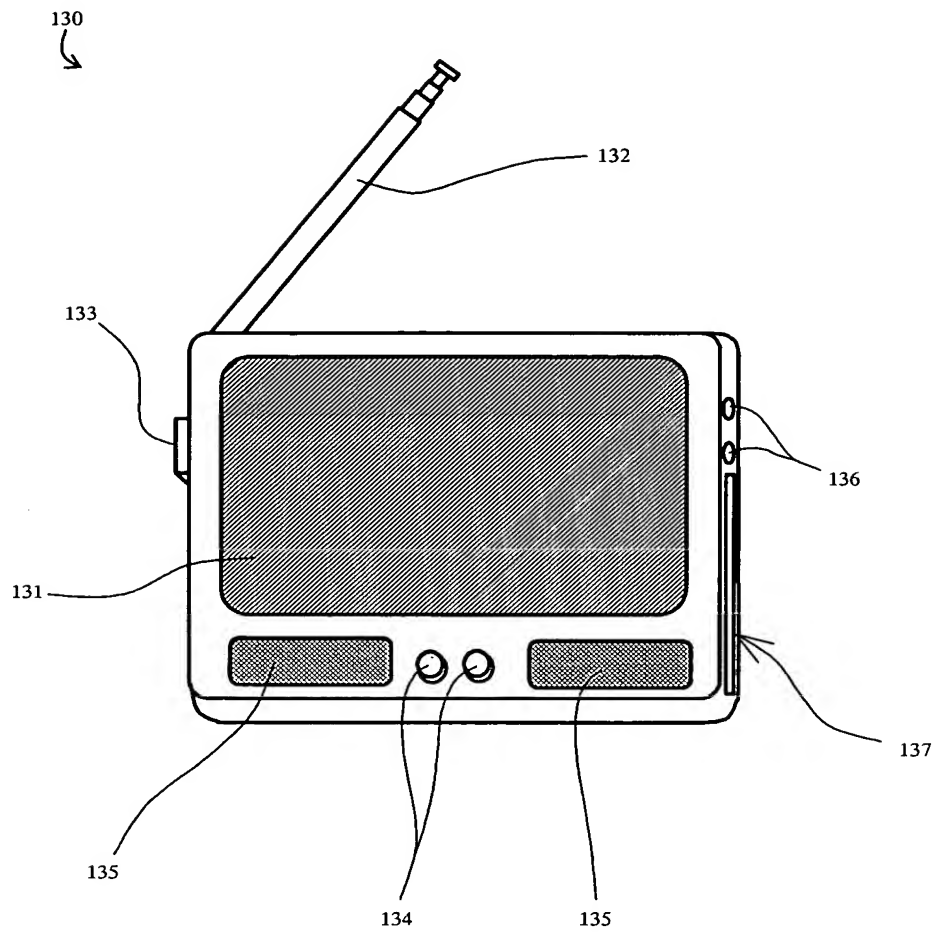


Fig. 17

140
↙

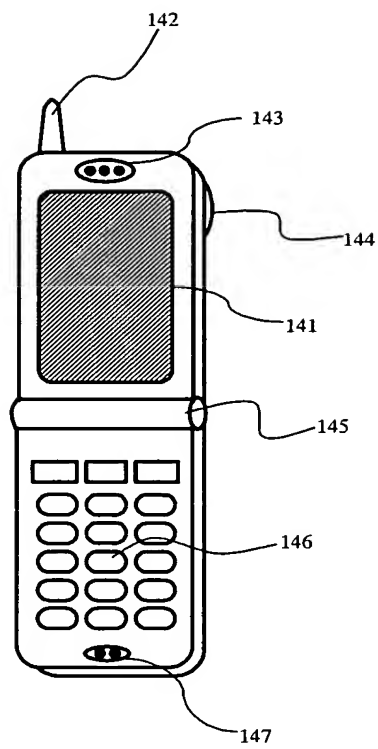


Fig. 18

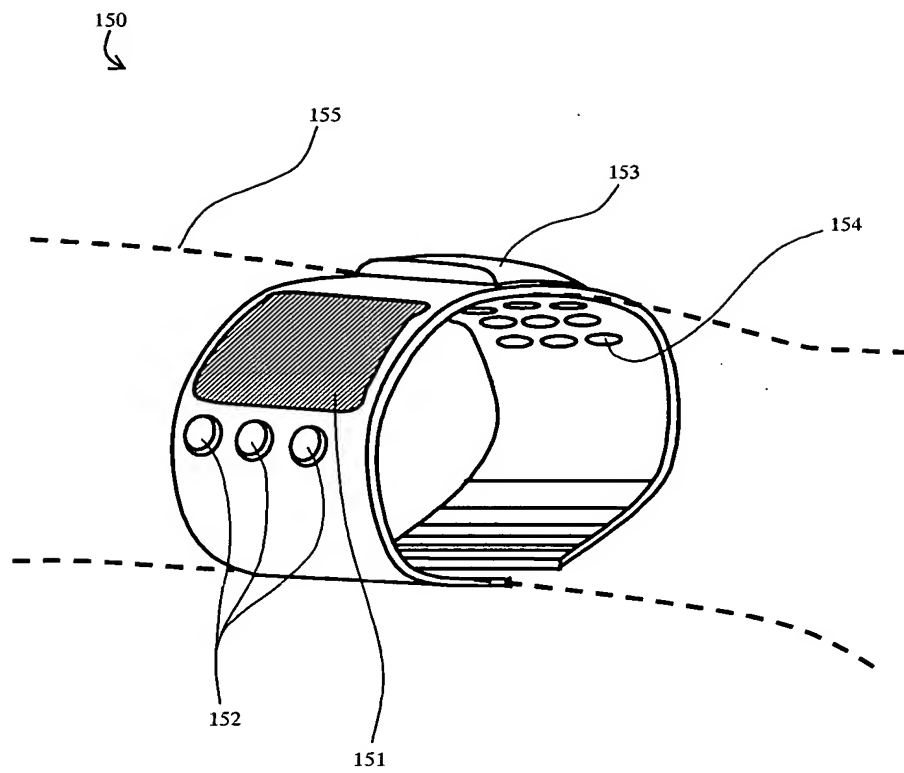


Fig. 19

REFERENCE MARK (1)

- 1 Substrate
 - 2 Gate electrode
 - 3 Gate insulating layer
 - 4 Semiconductor layer
 - 5 Source electrode
 - 6 Drain electrode
 - 7 Plastic substrate
 - 8 Particle
 - 9 Organic semiconductive material
- 100 TFT
- 101 Plastic substrate
 - 102 Organic EL layer
 - 103 Transparent electrode
 - 104 Protective film
 - 105 Source electrode line
 - 106 Gate electrode line
 - 110 TFT drive circuit
 - 111 Gate electrode
 - 112 Gate insulating layer
 - 113 Semiconductor layer
 - 114 Source electrode
 - 115 Drain electrode
 - 116 Pixel electrode
 - 117 Insulating layer
 - 120 Radio ID tag
 - 121 Plastic substrate
 - 122 Antenna portion
 - 123 Memory IC portion
 - 130 Portable TV
 - 131 Display portion
 - 132 Receiving portion
 - 133 Power switch
 - 134 Operation switch
 - 135 Sound output device

REFERENCE MARK (2)

- 136 Input/output terminal
- 137 Recording media insertion portion
- 140 Cellular phone
- 141 Display portion
- 142 Receiving/sending portion
- 143 Sound output portion
- 144 Camera portion
- 145 Movable folding portion
- 146 Operation switch
- 147 Sound input portion
- 150 Portable medical device
- 151 Display portion
- 152 Operation switch
- 153 Medical treatment portion
- 154 Transdermal contact portion
- 155 Arm
- 200 TFT
- 300 Semiconductor property evaluation sample
- 400 Sectional surface